



Data Sheet

March 2009

4A, 1200V Ultrafast Diodes

The RURD4120S9A_F085 are ultrafast diodes with soft recovery characteristics ($t_{rr} < 70$ ns). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/ clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49036.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURD4120S9A_F085	TO-252	UR4120

Symbol



Features

•	Ultrafast with Soft	Recovery													<70ns	5
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- Avalanche Energy Rated
- Planar Construction
- Qualified to ACE Q101
- RoHS Compliant

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-252



Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

	RURD4120S9A_F085	UNITS
Peak Repetitive Reverse Voltage V _{RRM}	1200	V
Working Peak Reverse VoltageV _{RWM}	1200	V
DC Blocking Voltage	1200	V
Average Rectified Forward Current	4	А
Repetitive Peak Surge Current I _{FRM} (Square Wave, 20kHz)	8	A
Nonrepetitive Peak Surge Current I _{FSM} (Halfwave, 1 Phase, 60Hz)	40	A
Maximum Power Dissipation	50	W
Avalanche Energy (See Figures 10 and 11) E _{AVL}	10	mJ
Operating and Storage Temperature	-65 to 175	OO

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SYMBOL	TEST CONDITION	MIN	ТҮР	MAX	UNITS
V _F	I _F = 4A	-	-	2.1	V
	I _F = 4A, T _C = 150 ^o C	-	-	1.9	V
I _R	V _R = 1200V	-	-	100	μΑ
	V _R = 1200V, T _C = 150 ^o C	-	-	500	μΑ
t _{rr}	$I_{F} = 1A, dI_{F}/dt = 200A/\mu s$	-	-	70	ns
	$I_F = 4A$, $dI_F/dt = 200A/\mu s$	-	-	90	ns
t _a	$I_F = 4A$, $dI_F/dt = 200A/\mu s$	-	40	-	ns
t _b	$I_F = 4A$, $dI_F/dt = 200A/\mu s$	-	28	-	ns
Q _{RR}	I _F = 4A, dI _F /dt = 200A/μs	-	335	-	nC
CJ	$V_{R} = 10V, I_{F} = 0A$	-	15	-	pF
R _{θJC}		-	-	3	°C/W

Electrical Specifications T_C = 25°C, Unless Otherwise Specified

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300µs, D = 2%).

 I_{R} = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

 t_a = Time to reach peak reverse current (See Figure 9).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

 Q_{RR} = Reverse recovery time.

 C_J = Junction capacitance.

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

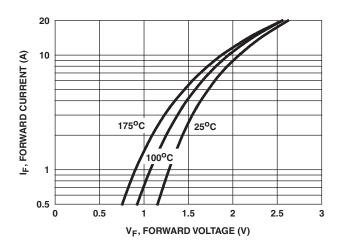


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

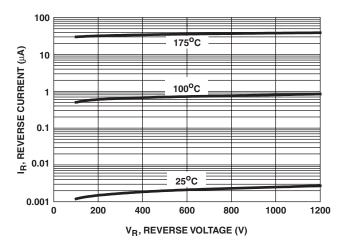


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

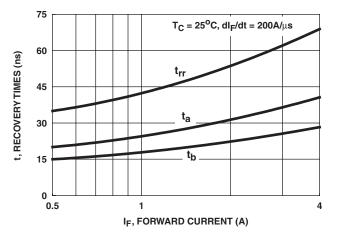
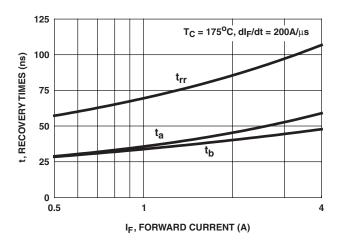


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT





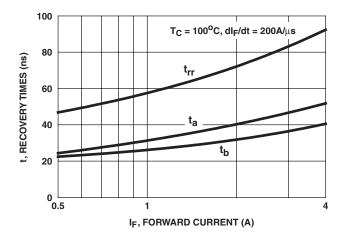


FIGURE 4. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

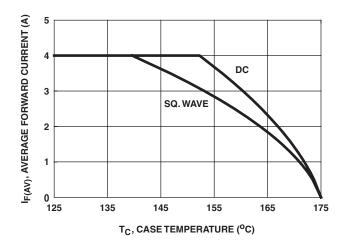


FIGURE 6. CURRENT DERATING CURVE

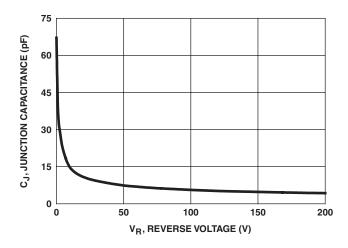


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

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Test Circuits and Waveforms

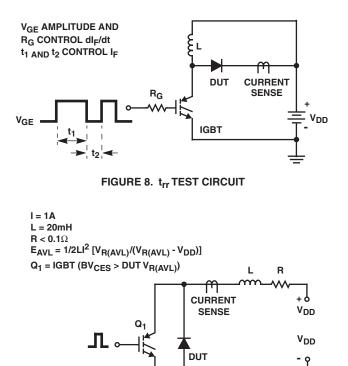


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

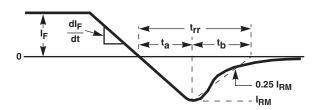


FIGURE 9. trr WAVEFORMS AND DEFINITIONS

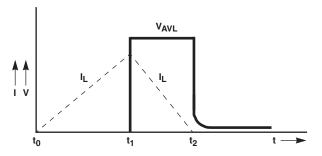
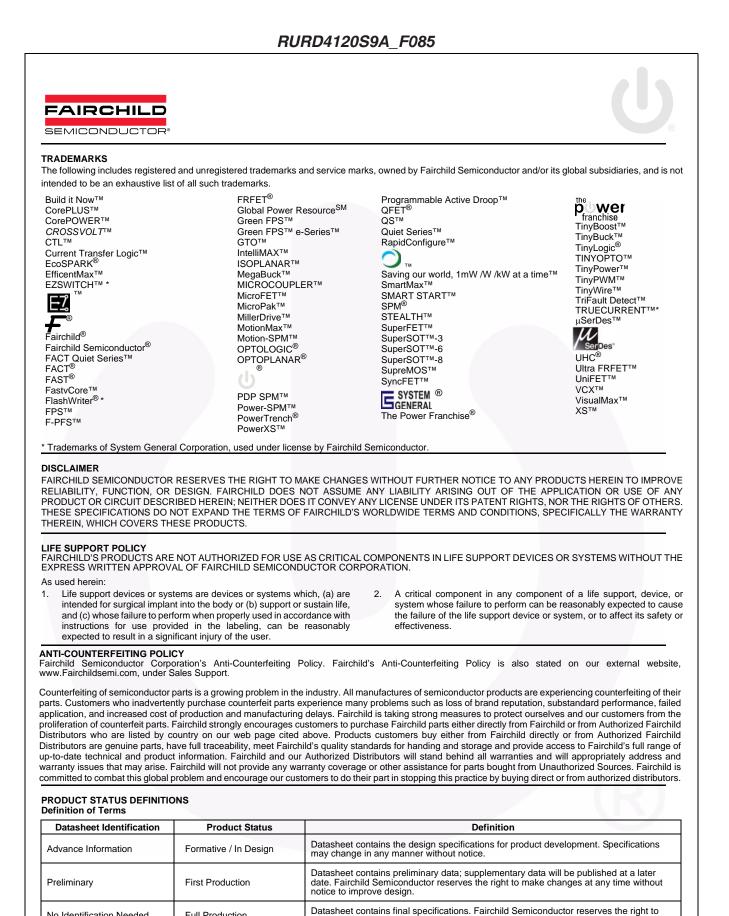


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS



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No Identification Needed

Obsolete

Full Production

Not In Production

make changes at any time without notice to improve the design.

Semiconductor. The datasheet is for reference information only.

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Datasheet contains specifications on a product that is discontinued by Fairchild

RURD4120S9A F085 Rev. A

Rev. 139